

## Product Summary

| $V_{(BR)DSS}$ | $R_{DS(ON) \max}$                      | $I_D \max$<br>$T_A = 25^\circ\text{C}$ |
|---------------|--|--|
| -20V          | 54m $\Omega$ @ $V_{GS} = -4.5\text{V}$ | -2.5A                                  |
|               | 90m $\Omega$ @ $V_{GS} = -1.8\text{V}$ | -1.8A                                  |

## Description and Applications

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

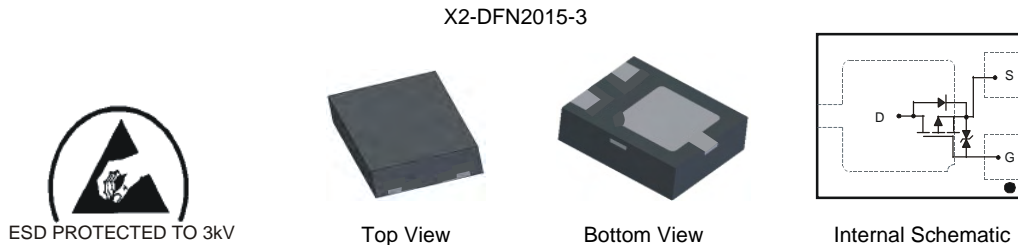
- Backlighting
- Power Management Functions
- DC-DC Converters
- 

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 3kV**
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device, Halogen and Antimony Free (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: X2-DFN2015-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

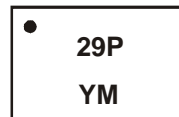


## Ordering Information (Note 3)

| Part Number   | Case         | Packaging        |
|---------------|--------------|------------------|
| DMP2069UFY4-7 | X2-DFN2015-3 | 3000/Tape & Reel |

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



29P = Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: W = 2009)  
 M = Month (ex: 9 = September)

### Date Code Key

| Year | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 |
|------|------|------|------|------|------|------|------|
| Code | W    | X    | Y    | Z    | A    | B    | C    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                    |              |                       | Symbol           | Value | Units |
|-----------------------------------|--------------|-----------------------|------------------|-------|-------|
| Drain-Source Voltage              |              |                       | V <sub>DSS</sub> | -20   | V     |
| Gate-Source Voltage               |              |                       | V <sub>GSS</sub> | ±8    | V     |
| Continuous Drain Current (Note 4) | Steady State | T <sub>A</sub> = 25°C | I <sub>D</sub>   | -2.5  | A     |
|                                   |              | T <sub>A</sub> = 70°C |                  | -2.2  |       |
| Pulsed Drain Current (Note 5)     |              |                       | I <sub>DM</sub>  | -12   | A     |

**Thermal Characteristics**

| Characteristic   | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 4)                                     | P <sub>D</sub>                    | 0.53        | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C | R <sub>θJA</sub>                  | 231         | °C/W |
| Operating and Storage Temperature Range                        | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                            | Symbol              | Min  | Typ   | Max  | Unit | Test Condition   |
|---|---------------------|------|-------|------|------|--|
| <b>OFF CHARACTERISTICS (Note 6)</b>       |                     |      |       |      |      |  |
| Drain-Source Breakdown Voltage            | BV <sub>DSS</sub>   | -20  | —     | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA  |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>    | —    | —     | -1.0 | μA   | T <sub>J</sub> = 25°C, V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V                              |
| Gate-Source Leakage                       | I <sub>GSS</sub>    | —    | —     | ±10  | μA   | V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V  |
| <b>ON CHARACTERISTICS (Note 6)</b>        |                     |      |       |      |      |  |
| Gate Threshold Voltage                    | V <sub>GS(th)</sub> | -0.3 | -0.55 | -1.0 | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA                                      |
| Static Drain-Source On-Resistance         | R <sub>DS(ON)</sub> | —    | 36    | 54   | mΩ   | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.5A  |
|   |                     |      | 46    | 69   |      |  |
|   |                     |      | 60    | 90   |      |  |
| Forward Transfer Admittance               | Y <sub>fs</sub>     | —    | 8     | —    | S    | V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.5A  |
| <b>DYNAMIC CHARACTERISTICS (Note 7)</b>   |                     |      |       |      |      |  |
| Input Capacitance                         | C <sub>iss</sub>    | —    | 214   | —    | pF   | V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V<br>f = 1.0MHz                                       |
| Output Capacitance                        | C <sub>oss</sub>    | —    | 104   | —    | pF   |  |
| Reverse Transfer Capacitance              | C <sub>rss</sub>    | —    | 25    | —    | pF   |  |
| Gate Resistnace                           | R <sub>g</sub>      | —    | 250   | —    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz   |
| <b>SWITCHING CHARACTERISTICS (Note 7)</b> |                     |      |       |      |      |  |
| Total Gate Charge                         | Q <sub>g</sub>      | —    | 9.1   | —    | nC   | V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -4A                            |
| Gate-Source Charge                        | Q <sub>gs</sub>     | —    | 1.5   | —    | nC   |  |
| Gate-Drain Charge                         | Q <sub>gd</sub>     | —    | 1.7   | —    | nC   |  |
| Turn-On Delay Time                        | t <sub>D(on)</sub>  | —    | 80.4  | 160  | ns   | V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V,<br>R <sub>D</sub> = 2.5Ω, R <sub>G</sub> = 3.0Ω |
| Turn-On Rise Time                         | t <sub>r</sub>      | —    | 155.1 | 210  | ns   |  |
| Turn-Off Delay Time                       | t <sub>D(off)</sub> | —    | 688.1 | 1376 | ns   |  |
| Turn-Off Fall Time                        | t <sub>f</sub>      | —    | 423.8 | 848  | ns   |  |

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

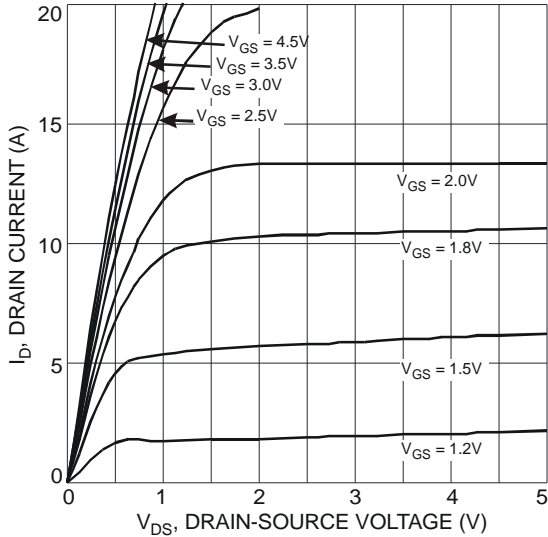


Fig. 1 Typical Output Characteristic

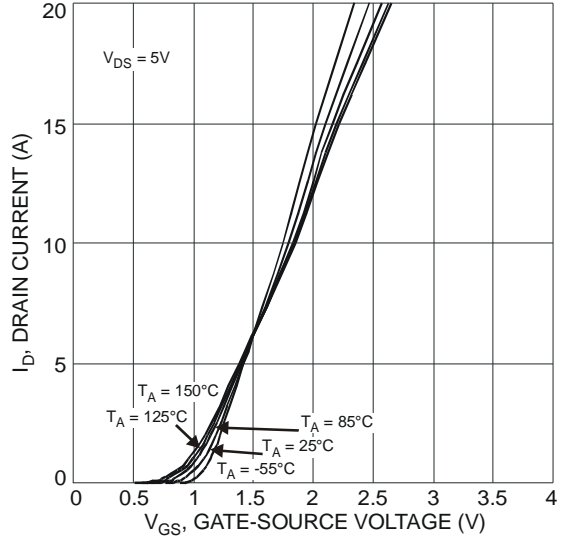


Fig. 2 Typical Transfer Characteristic

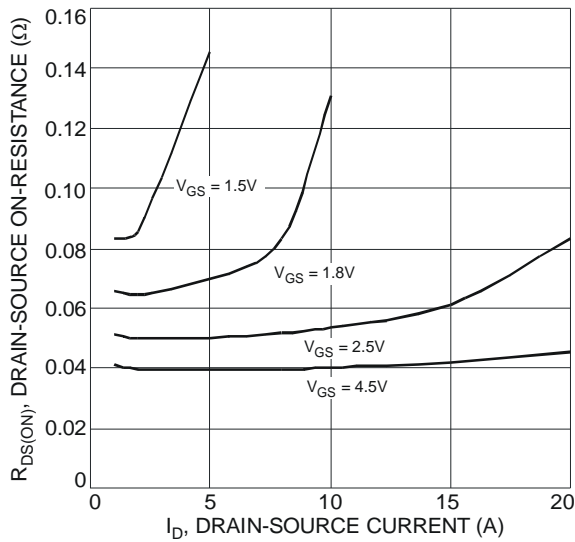


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

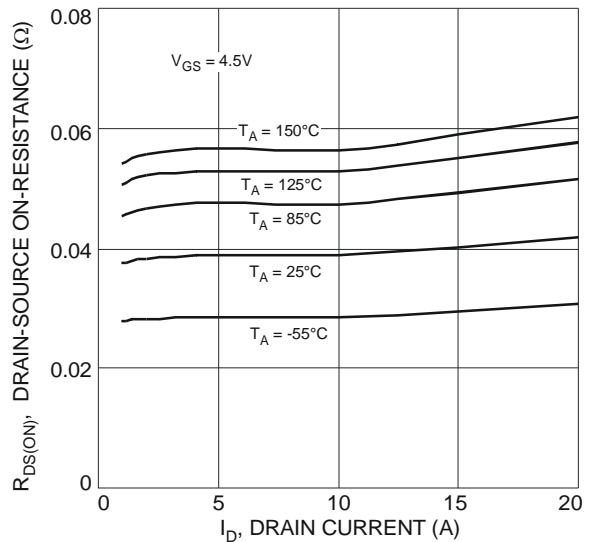


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

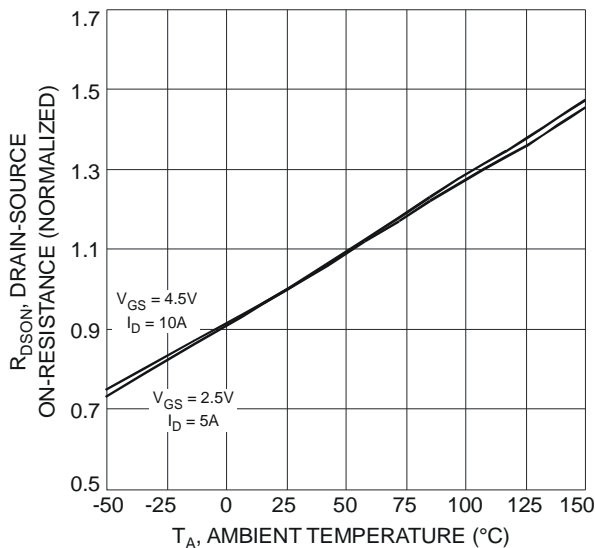


Fig. 5 On-Resistance Variation with Temperature

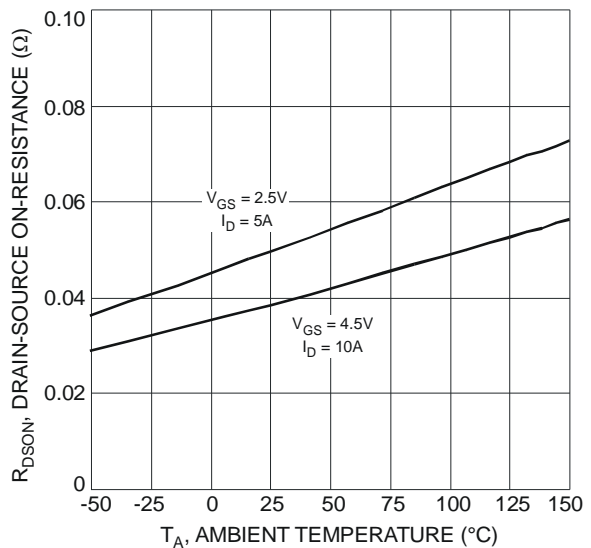


Fig. 6 On-Resistance Variation with Temperature

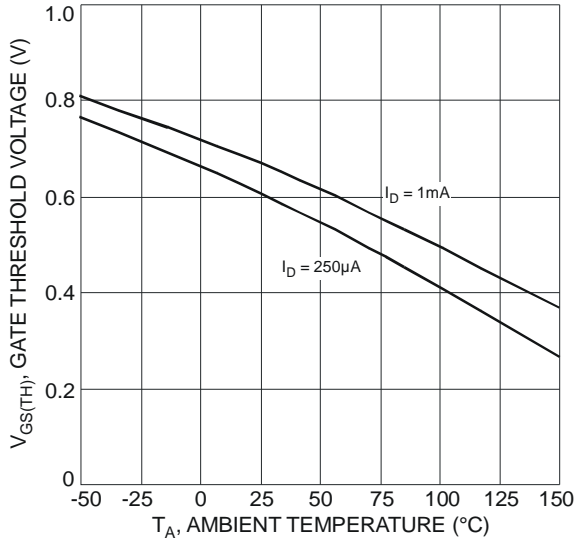


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

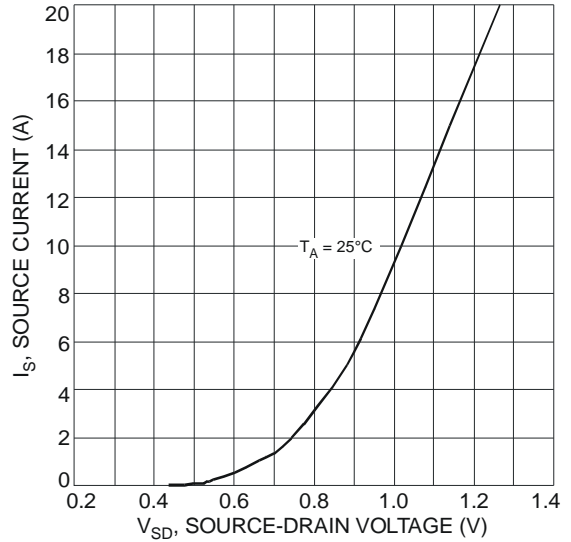


Fig. 8 Diode Forward Voltage vs. Current

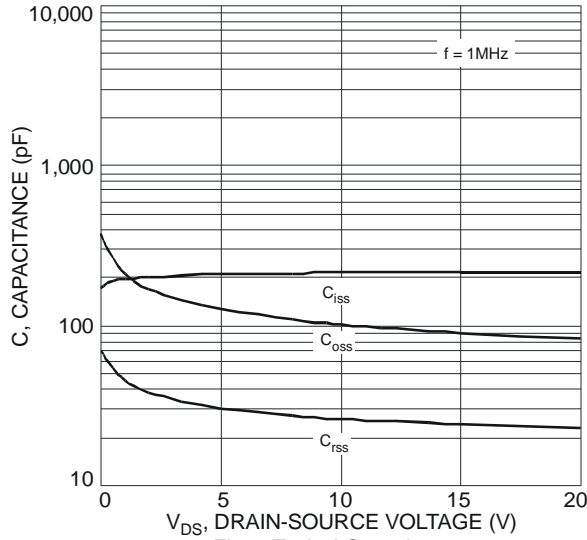


Fig. 9 Typical Capacitance

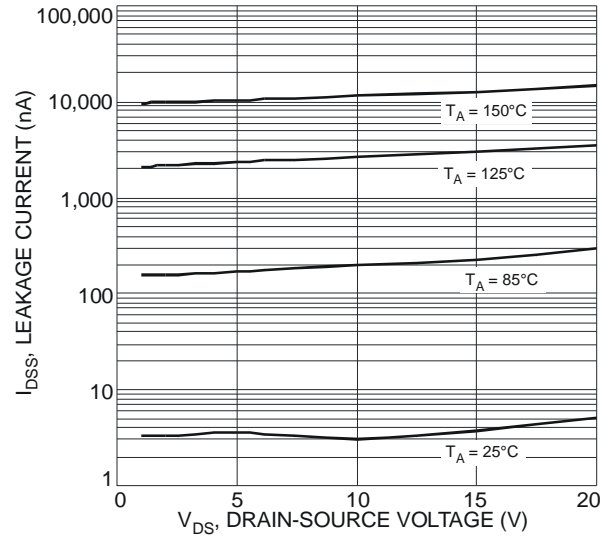


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

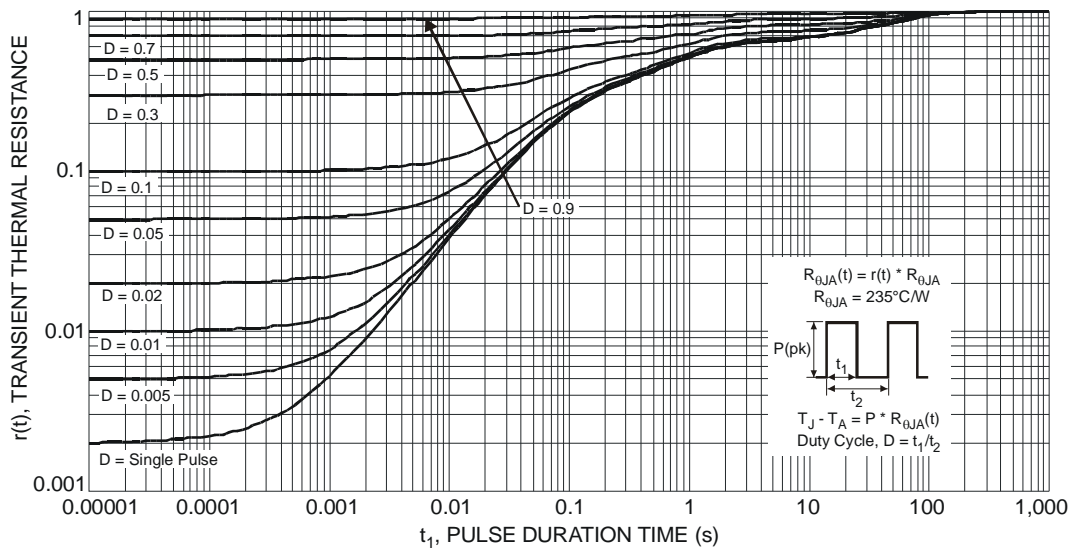
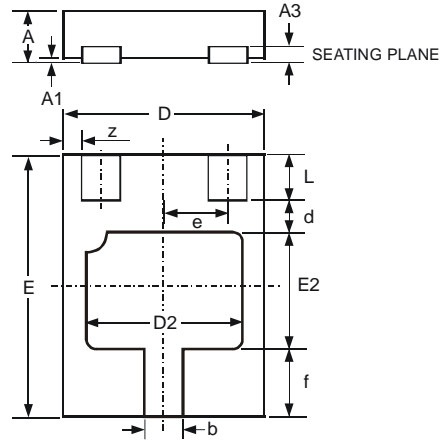


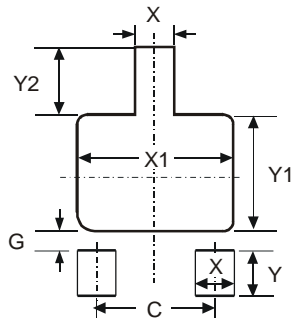
Fig. 11 Transient Thermal Response

**Package Outline Dimensions**



| X2-DFN2015-3         |      |       |       |
|----------------------|------|-------|-------|
| Dim                  | Min  | Max   | Typ   |
| A                    | -    | 0.40  | -     |
| A1                   | 0    | 0.05  | 0.02  |
| A3                   | -    | -     | 0.13  |
| b                    | 0.20 | 0.30  | 0.25  |
| d                    | -    | -     | 0.30  |
| D                    | 1.45 | 1.575 | 1.50  |
| D2                   | 1.00 | 1.20  | 1.10  |
| e                    | -    | -     | 0.50  |
| E                    | 1.95 | 2.075 | 2.00  |
| E2                   | 0.70 | 0.90  | 0.80  |
| f                    | -    | -     | 0.60  |
| L                    | 0.25 | 0.35  | 0.30  |
| z                    | -    | -     | 0.125 |
| All Dimensions in mm |      |       |       |

**Suggested Pad Layout**



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 1.00          |
| G          | 0.15          |
| X          | 0.31          |
| X1         | 1.30          |
| Y          | 0.50          |
| Y1         | 1.00          |
| Y2         | 0.65          |

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Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: [ocean@oceanchips.ru](mailto:ocean@oceanchips.ru)

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А